

ABSTRACT OF THE DISCLOSURE

In one illustrative embodiment, a system is comprised of a semiconductor processing tool, an etcher, a metrology tool, and a controller. The semiconductor processing tool is capable of forming a process layer above a semiconducting substrate. The etcher is capable 5 of removing at least a portion of the process layer. The metrology tool is capable of measuring a first depth of the etch at a first location in a first preselected region of the semiconducting substrate. The controller is capable of comparing the first depth to a desired depth, and varying the temperature of a subsequently processed semiconducting substrate in a region corresponding to the first preselected region in response to the first depth being 10 different from the desired depth.

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